

# Small Signal Diodes

## MMBD1201 - MMBD1205

### Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### ABSOLUTE MAXIMUM RATINGS (Note 1, Note 2)

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$V_{RRM}$	Maximum Repetitive Reverse Voltage	100	V
$I_{F(AV)}$	Average Rectified Forward Current	200	mA
$I_{FSM}$	Non-Repetitive Peak Forward Surge Current	Pulse Width = 1.0 s	1.0
		Pulse Width = 1.0 $\mu\text{s}$	2.0
$T_{STG}$	Storage Temperature Range	-55 to + 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature	150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. These ratings are based on a maximum junction temperature of  $150^\circ\text{C}$ .
2. These are steady-state limits. ON Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

### THERMAL CHARACTERISTICS

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

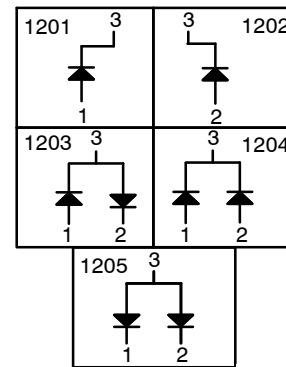
Symbol	Parameter	Value	Unit
$P_D$	Power Dissipation	350	mW
	Derate Above $25^\circ\text{C}$	2.8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ\text{C}/\text{W}$



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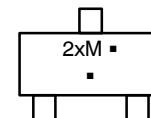
[www.onsemi.com](http://www.onsemi.com)

### CONNECTION DIAGRAM



SOT-23  
CASE 318-08

### MARKING DIAGRAM



- 2x = Specific Device Code
- x = 4, 5, 6, 7, 8
- M = Date Code
- = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
MMBD1201, MMBD1202, MMBD1203, MMBD1204, MMBD1205	SOT-23 (Pb-Free Halide Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

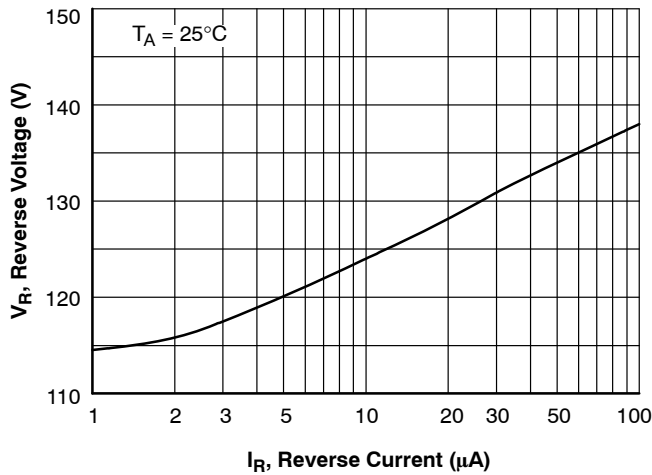
# MMBD1201 – MMBD1205

**ELECTRICAL CHARACTERISTICS** Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

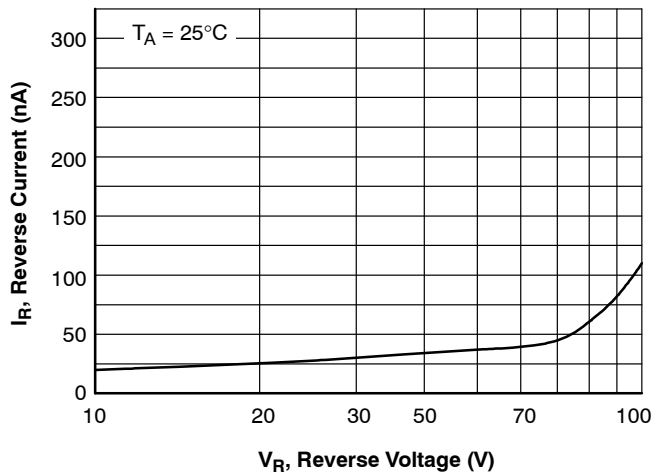
Symbol	Parameter	Conditions	Min.	Max.	Unit
$V_R$	Breakdown Voltage	$I_R = 100 \mu\text{A}$	100	–	V
$V_F$	Forward Voltage	$I_F = 1.0 \text{ mA}$	550	600	mV
		$I_F = 10 \text{ mA}$	660	740	mV
		$I_F = 100 \text{ mA}$	820	920	mV
		$I_F = 200 \text{ mA}$	0.87	1.0	V
		$I_F = 300 \text{ mA}$	–	1.1	V
$I_R$	Reverse Current	$V_R = 20 \text{ V}$	–	25	nA
		$V_R = 50 \text{ V}$	–	50	nA
		$V_R = 50 \text{ V}, T_A = 150^\circ\text{C}$	–	100	$\mu\text{A}$
$C_T$	Total Capacitance	$V_R = 0 \text{ V}, f = 1.0 \text{ MHz}$	–	2.0	pF
$t_{rr}$	Reverse Recovery Time	$I_F = I_R = 10 \text{ mA}, I_{RR} = 1.0 \text{ mA}, R_L = 100 \Omega$	–	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## TYPICAL PERFORMANCE CHARACTERISTICS



**Figure 1. Reverse Voltage vs. Reverse Current**  
 $V_R$  @  $I_R = 1.0$  to  $100 \mu\text{A}$



**Figure 2. Reverse Current vs. Reverse Voltage**  
 $I_R$  @  $V_R = 10$  to  $100 \text{ V}$

# MMBD1201 – MMBD1205

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

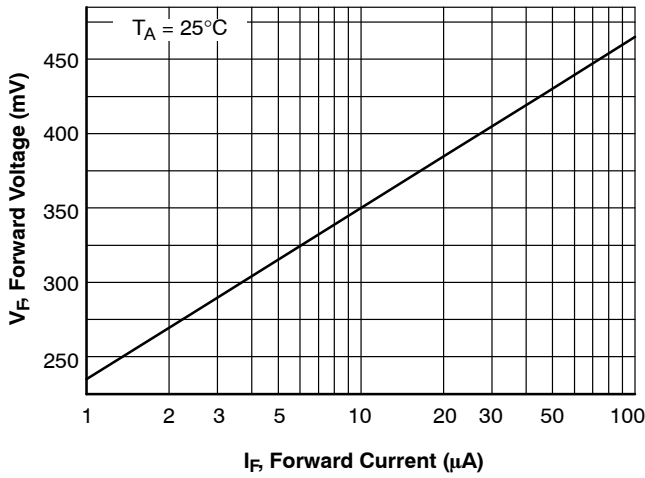


Figure 3. Forward Voltage vs. Forward Current  
 $V_F$  @  $I_F = 1.0$  to  $100 \mu\text{A}$

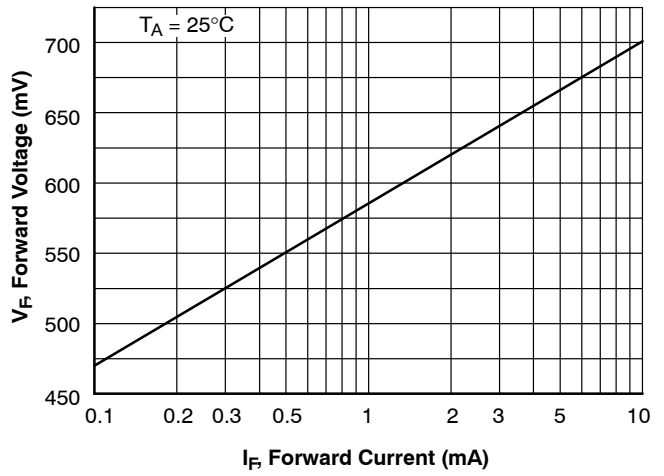


Figure 4. Forward Voltage vs. Forward Current  
 $V_F$  @  $I_F = 0.1$  to  $10 \text{ mA}$

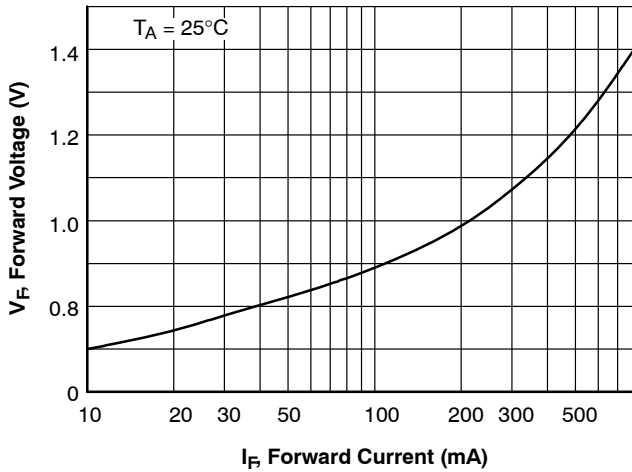


Figure 5. Forward Voltage vs. Forward Current  
 $V_F$  @  $I_F = 10$  to  $800 \text{ mA}$

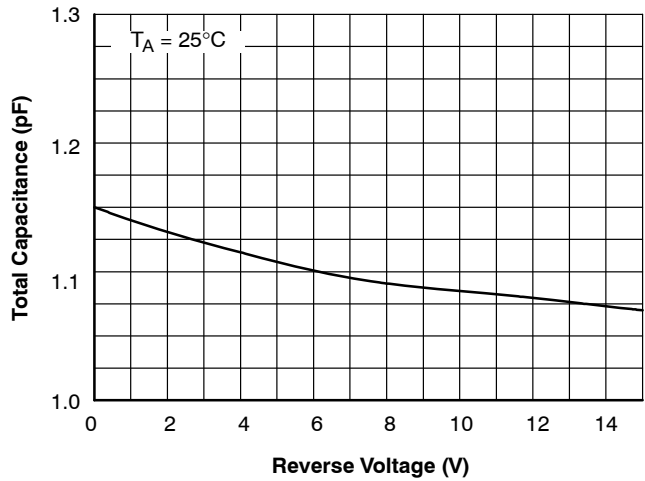


Figure 6. Total Capacitance vs. Reverse Voltage

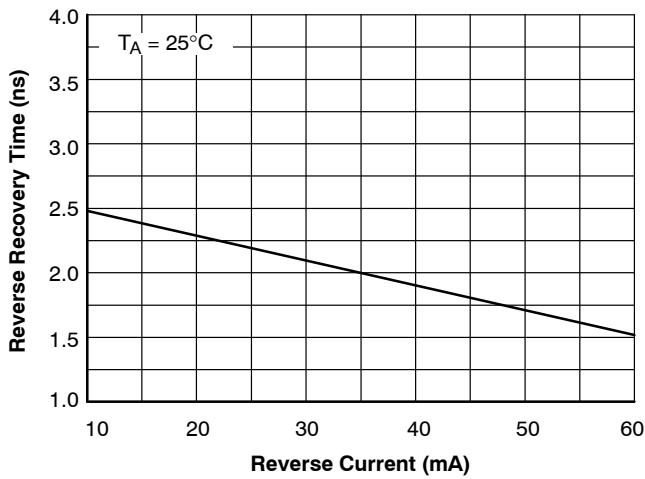


Figure 7. Reverse Recovery Time vs. Reverse Current

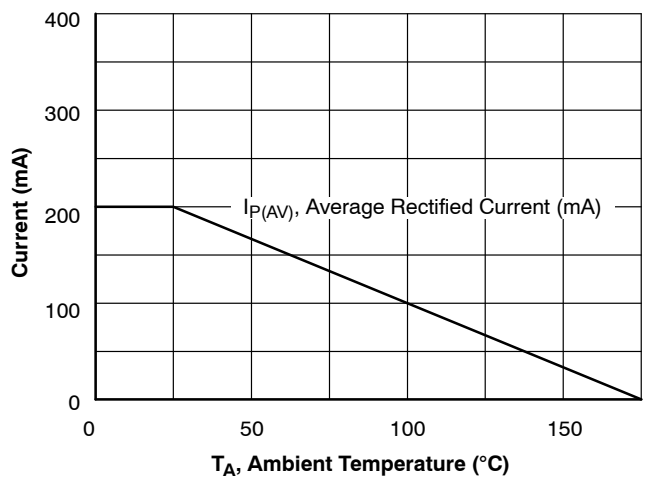


Figure 8. Average Rectified Current ( $I_{F(AV)}$ ) vs. Ambient Temperature ( $T_A$ )

# MMBD1201 – MMBD1205

## TYPICAL PERFORMANCE CHARACTERISTICS (continued)

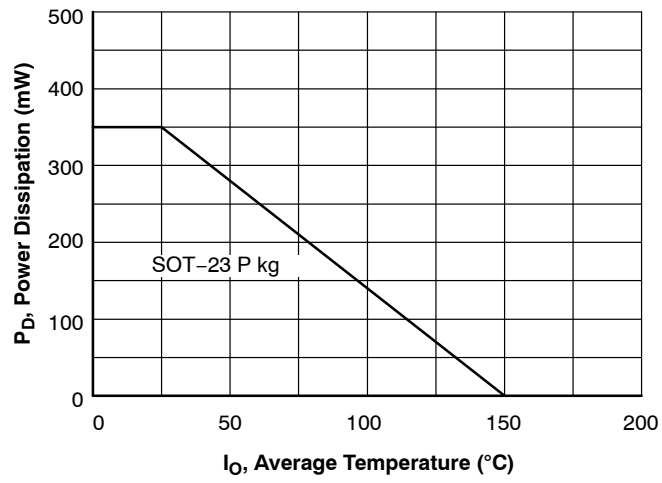
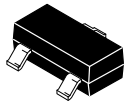


Figure 9. Power Derating Curve

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

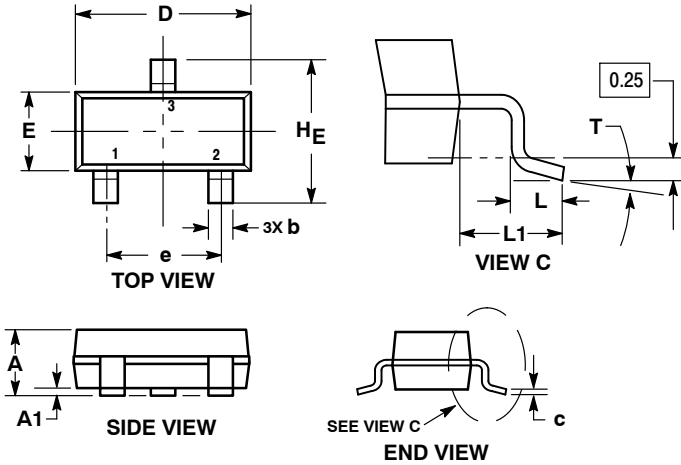
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**SOT-23 (TO-236)**  
CASE 318-08  
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1

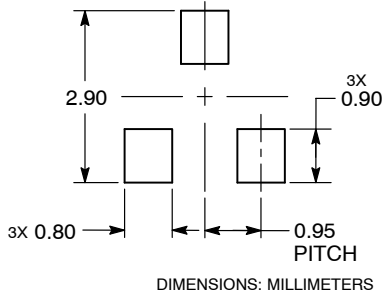


**NOTES:**

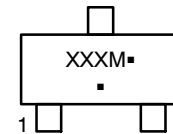
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

**RECOMMENDED SOLDERING FOOTPRINT**



**GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code  
M = Date Code  
■ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.

STYLE 1 THRU 5:  
CANCELLED

STYLE 6:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 7:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 8:  
PIN 1. ANODE  
2. NO CONNECTION  
3. CATHODE

STYLE 9:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 10:  
PIN 1. DRAIN  
2. SOURCE  
3. GATE

STYLE 11:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 12:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 13:  
PIN 1. SOURCE  
2. DRAIN  
3. GATE

STYLE 14:  
PIN 1. CATHODE  
2. GATE  
3. ANODE

STYLE 15:  
PIN 1. GATE  
2. CATHODE  
3. ANODE

STYLE 16:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE

STYLE 17:  
PIN 1. NO CONNECTION  
2. ANODE  
3. CATHODE

STYLE 18:  
PIN 1. NO CONNECTION  
2. CATHODE  
3. ANODE

STYLE 19:  
PIN 1. CATHODE  
2. ANODE  
3. CATHODE-ANODE

STYLE 20:  
PIN 1. CATHODE  
2. ANODE  
3. GATE

STYLE 21:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 22:  
PIN 1. RETURN  
2. OUTPUT  
3. INPUT

STYLE 23:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 24:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE

STYLE 25:  
PIN 1. ANODE  
2. CATHODE  
3. GATE

STYLE 26:  
PIN 1. CATHODE  
2. ANODE  
3. NO CONNECTION

STYLE 27:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

STYLE 28:  
PIN 1. ANODE  
2. ANODE  
3. ANODE

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